

## Thyristor/Diode and Thyristor/Thyristor (SUPER MAGN-A-PAK Power Modules), 500 A



SUPER MAGN-A-PAK

### PRODUCT SUMMARY

$I_{T(AV)}$ ,  $I_{F(AV)}$

500 A

### FEATURES

- High current capability
- High surge capability
- Industrial standard package
- 3000  $V_{RMS}$  isolating voltage with non-toxic substrate
- UL approved file E78996 
- Compliant to RoHS directive 2002/95/EC
- Designed and qualified for industrial level



**RoHS**  
COMPLIANT

### TYPICAL APPLICATIONS

- Motor starters
- DC motor controls - AC motor controls
- Uninterruptable power supplies

### MAJOR RATINGS AND CHARACTERISTICS

| SYMBOL                    | CHARACTERISTICS | VALUES      | UNITS              |
|---------------------------|-----------------|-------------|--------------------|
| $I_{T(AV)}$ , $I_{F(AV)}$ | 82 °C           | 500         | A                  |
| $I_{T(RMS)}$              |                 | 785         | A                  |
|                           | $T_C$           | 82          | °C                 |
| $I_{TSM}$                 | 50 Hz           | 17.8        | kA                 |
|                           | 60 Hz           | 18.7        |                    |
| $I^2t$                    | 50 Hz           | 1591        | kA <sup>2</sup> s  |
|                           | 60 Hz           | 1452        |                    |
| $I^2\sqrt{t}$             |                 | 15 910      | kA <sup>2</sup> √s |
| $V_{RRM}$                 | Range           | 800 to 1600 | V                  |
| $T_{Stg}$                 | Range           | - 40 to 150 | °C                 |
| $T_J$                     | Range           | - 40 to 130 |                    |

### ELECTRICAL SPECIFICATIONS

#### VOLTAGE RATINGS

| TYPE NUMBER | VOLTAGE CODE | $V_{RRM}/V_{DRM}$ , MAXIMUM REPETITIVE<br>PEAK REVERSE VOLTAGE<br>V | $V_{RSM}$ , MAXIMUM NON-REPETITIVE<br>PEAK REVERSE VOLTAGE<br>V | $I_{RRM}/I_{DRM}$ MAXIMUM<br>AT $T_J = T_J$ MAXIMUM<br>mA |
|-------------|--------------|---------------------------------------------------------------------|-----------------------------------------------------------------|-----------------------------------------------------------|
| VSK.500     | 08           | 800                                                                 | 900                                                             | 100                                                       |
|             | 12           | 1200                                                                | 1300                                                            |                                                           |
|             | 14           | 1400                                                                | 1500                                                            |                                                           |
|             | 16           | 1600                                                                | 1700                                                            |                                                           |

| ON-STATE CONDUCTION                                            |                              |                                                                                        |                           |                                                   |        |                    |
|----------------------------------------------------------------|------------------------------|----------------------------------------------------------------------------------------|---------------------------|---------------------------------------------------|--------|--------------------|
| PARAMETER                                                      | SYMBOL                       | TEST CONDITIONS                                                                        |                           |                                                   | VALUES | UNITS              |
| Maximum average on-state current at case temperature           | $I_{T(AV)}$ ,<br>$I_{F(AV)}$ | 180° conduction, half sine wave                                                        |                           |                                                   | 500    | A                  |
|                                                                |                              |                                                                                        |                           |                                                   | 82     | °C                 |
| Maximum RMS on-state current                                   | $I_{T(RMS)}$                 | 180° conduction, half sine wave at $T_C = 82\text{ °C}$                                |                           |                                                   | 785    | A                  |
| Maximum peak, one-cycle, non-repetitive on-state surge current | $I_{TSM}$ ,<br>$I_{FSM}$     | t = 10 ms                                                                              | No voltage reapplied      | Sinusoidal half wave, initial $T_J = T_J$ maximum | 17.8   | kA                 |
|                                                                |                              | t = 8.3 ms                                                                             |                           |                                                   | 18.7   |                    |
|                                                                |                              | t = 10 ms                                                                              | 100 % $V_{RRM}$ reapplied |                                                   | 15.0   |                    |
|                                                                |                              | t = 8.3 ms                                                                             |                           |                                                   | 15.7   |                    |
| Maximum $I^2t$ for fusing                                      | $I^2t$                       | t = 10 ms                                                                              | No voltage reapplied      |                                                   | 1591   | kA <sup>2</sup> s  |
|                                                                |                              | t = 8.3 ms                                                                             |                           |                                                   | 1452   |                    |
|                                                                |                              | t = 10 ms                                                                              | 100 % $V_{RRM}$ reapplied |                                                   | 1125   |                    |
|                                                                |                              | t = 8.3 ms                                                                             |                           |                                                   | 1027   |                    |
| Maximum $I^2\sqrt{t}$ for fusing                               | $I^2\sqrt{t}$                | t = 0.1 ms to 10 ms, no voltage reapplied                                              |                           |                                                   | 15 910 | kA <sup>2</sup> √s |
| Low level value or threshold voltage                           | $V_{T(TO)1}$                 | (16.7 % $\times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)}$ , $T_J = T_J$ maximum |                           |                                                   | 0.85   | V                  |
| High level value of threshold voltage                          | $V_{T(TO)2}$                 | (I $> \pi \times I_{T(AV)}$ ), $T_J = T_J$ maximum                                     |                           |                                                   | 0.93   |                    |
| Low level value on-state slope resistance                      | $r_{t1}$                     | (16.7 % $\times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)}$ , $T_J = T_J$ maximum |                           |                                                   | 0.36   | mΩ                 |
| High level value on-state slope resistance                     | $r_{t2}$                     | (I $> \pi \times I_{T(AV)}$ ), $T_J = T_J$ maximum                                     |                           |                                                   | 0.32   |                    |
| Maximum on-state voltage drop                                  | $V_{TM}$                     | $I_{pk} = 1500\text{ A}$ , $T_J = 25\text{ °C}$ , $t_p = 10\text{ ms}$ sine pulse      |                           |                                                   | 1.50   | V                  |
| Maximum forward voltage drop                                   | $V_{FM}$                     | $I_{pk} = 1500\text{ A}$ , $T_J = 25\text{ °C}$ , $t_p = 10\text{ ms}$ sine pulse      |                           |                                                   | 1.50   | V                  |
| Maximum holding current                                        | $I_H$                        | $T_J = 25\text{ °C}$ , anode supply 12 V resistive load                                |                           |                                                   | 500    | mA                 |
| Maximum latching current                                       | $I_L$                        |                                                                                        |                           |                                                   | 1000   |                    |

| SWITCHING                                 |                |                                                                                                                                                |        |       |
|-------------------------------------------|----------------|------------------------------------------------------------------------------------------------------------------------------------------------|--------|-------|
| PARAMETER                                 | SYMBOL         | TEST CONDITIONS                                                                                                                                | VALUES | UNITS |
| Maximum rate of rise of turned-on current | di/dt          | T <sub>J</sub> = T <sub>J</sub> maximum, I <sub>TM</sub> = 400 A, V <sub>DRM</sub> applied                                                     | 1000   | A/μs  |
| Typical delay time                        | t <sub>d</sub> | Gate current 1 A, di <sub>g</sub> /dt = 1 A/μs<br>V <sub>d</sub> = 0.67 % V <sub>DRM</sub> , T <sub>J</sub> = 25 °C                            | 2.0    | μs    |
| Typical turn-off time                     | t <sub>q</sub> | I <sub>TM</sub> = 750 A; T <sub>J</sub> = T <sub>J</sub> maximum, di/dt = - 60 A/μs,<br>V <sub>R</sub> = 50 V, dV/dt = 20 V/μs, gate 0 V 100 Ω | 200    |       |

| BLOCKING                                           |                                        |                                                                                           |        |       |
|----------------------------------------------------|----------------------------------------|-------------------------------------------------------------------------------------------|--------|-------|
| PARAMETER                                          | SYMBOL                                 | TEST CONDITIONS                                                                           | VALUES | UNITS |
| Maximum critical rate of rise of off-state voltage | dV/dt                                  | T <sub>J</sub> = 130 °C, linear to V <sub>D</sub> = 80 % V <sub>DRM</sub>                 | 1000   | V/μs  |
| RMS insulation voltage                             | V <sub>INS</sub>                       | t = 1 s                                                                                   | 3000   | V     |
| Maximum peak reverse and off-state leakage current | I <sub>RRM</sub> ,<br>I <sub>DRM</sub> | T <sub>J</sub> = T <sub>J</sub> maximum, rated V <sub>DRM</sub> /V <sub>RRM</sub> applied | 100    | mA    |



# VSKT500-..PbF, VSKH500-..PbF, VSKL500-..PbF

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| TRIGGERING                                  |             |                                              |        |       |
|---------------------------------------------|-------------|----------------------------------------------|--------|-------|
| PARAMETER                                   | SYMBOL      | TEST CONDITIONS                              | VALUES | UNITS |
| Maximum peak gate power                     | $P_{GM}$    | $T_J = T_J$ maximum, $t_p \leq 5$ ms         | 10     | W     |
| Maximum peak average gate power             | $P_{G(AV)}$ | $T_J = T_J$ maximum, $f = 50$ Hz, $d\% = 50$ | 2.0    |       |
| Maximum peak positive gate current          | $+I_{GM}$   | $T_J = T_J$ maximum, $t_p \leq 5$ ms         | 3.0    | A     |
| Maximum peak positive gate voltage          | $+V_{GM}$   |                                              | 20     | V     |
| Maximum peak negative gate voltage          | $-V_{GM}$   |                                              | 5.0    |       |
| Maximum DC gate current required to trigger | $I_{GT}$    | $T_J = 25^\circ\text{C}$ , $V_{ak} 12$ V     | 200    | mA    |
| DC gate voltage required to trigger         | $V_{GT}$    |                                              | 3.0    | V     |
| DC gate current not to trigger              | $I_{GD}$    | $T_J = T_J$ maximum                          | 10     | mA    |
| DC gate voltage not to trigger              | $V_{GD}$    |                                              | 0.25   | V     |

| THERMAL AND MECHANICAL SPECIFICATIONS                            |              |                                                                                                                                          |                  |                  |
|------------------------------------------------------------------|--------------|------------------------------------------------------------------------------------------------------------------------------------------|------------------|------------------|
| PARAMETER                                                        | SYMBOL       | TEST CONDITIONS                                                                                                                          | VALUES           | UNITS            |
| Maximum junction operating temperature range                     | $T_J$        |                                                                                                                                          | - 40 to 130      | $^\circ\text{C}$ |
| Maximum storage temperature range                                | $T_{Stg}$    |                                                                                                                                          | - 40 to 150      |                  |
| Maximum thermal resistance, junction to case per junction        | $R_{thJC}$   | DC operation                                                                                                                             | 0.065            | K/W              |
| Maximum thermal resistance, case to heatsink                     | $R_{thC-hs}$ |                                                                                                                                          | 0.02             |                  |
| Mounting torque $\pm 10\%$<br>SMAP to heatsink<br>busbar to SMAP |              | A mounting compound is recommended and the torque should be rechecked after a period of 3 hours to allow for the spread of the compound. | 6 to 8           | Nm               |
|                                                                  |              |                                                                                                                                          | 12 to 15         |                  |
| Approximate weight                                               |              |                                                                                                                                          | 1500             | g                |
| Case style                                                       |              | See dimensions - link at the end of datasheet                                                                                            | SUPER MAGN-A-PAK |                  |

| $\Delta R_{thJC}$ CONDUCTION |                       |                        |                     |       |
|------------------------------|-----------------------|------------------------|---------------------|-------|
| CONDUCTION ANGLE             | SINUSOIDAL CONDUCTION | RECTANGULAR CONDUCTION | TEST CONDITIONS     | UNITS |
| 180°                         | 0.009                 | 0.006                  | $T_J = T_J$ maximum | K/W   |
| 120°                         | 0.011                 | 0.011                  |                     |       |
| 90°                          | 0.014                 | 0.015                  |                     |       |
| 60°                          | 0.021                 | 0.022                  |                     |       |
| 30°                          | 0.037                 | 0.038                  |                     |       |

## Note

- Table shows the increment of thermal resistance  $R_{thJC}$  when devices operate at different conduction angles than DC

# VSKT500-..PbF, VSKH500-..PbF, VSKL500-..PbF



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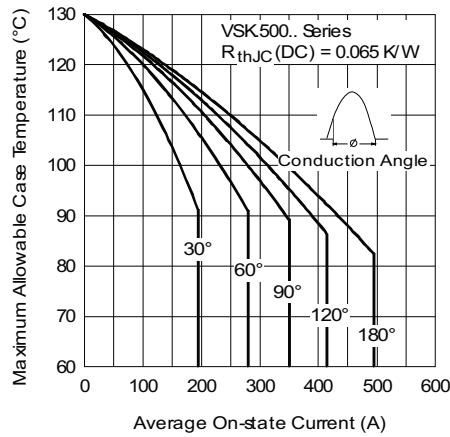


Fig. 1 - Current Ratings Characteristics

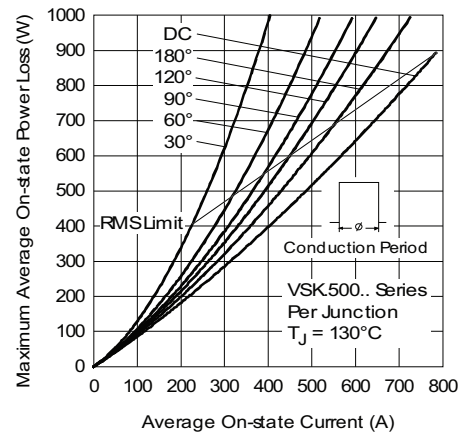


Fig. 4 - On-State Power Loss Characteristics

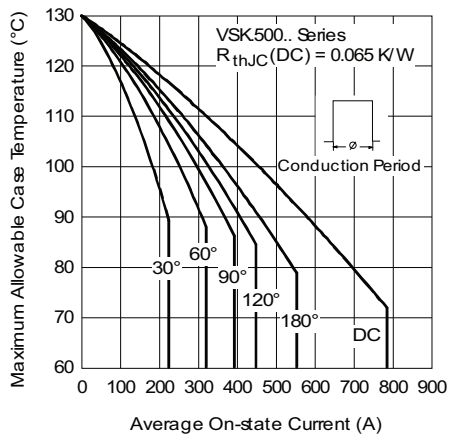


Fig. 2 - Current Ratings Characteristics

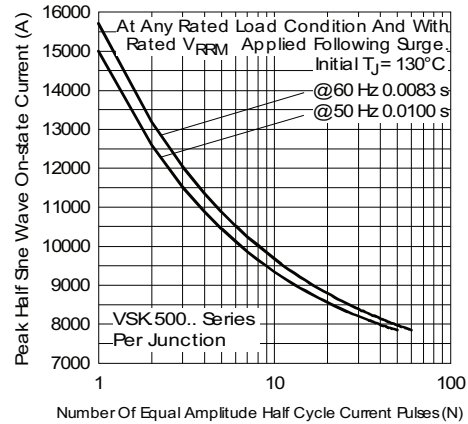


Fig. 5 - Maximum Non-Repetitive Surge Current

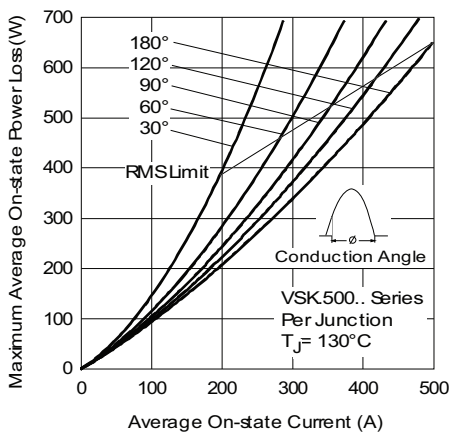


Fig. 3 - On-State Power Loss Characteristics

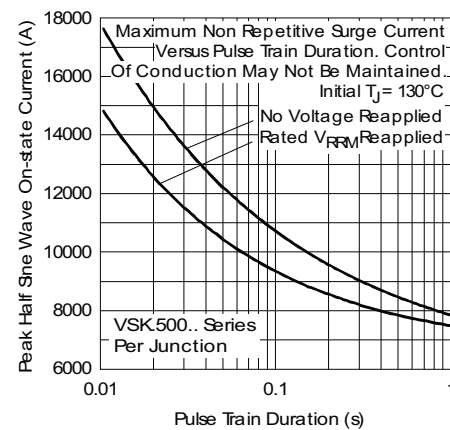


Fig. 6 - Maximum Non-Repetitive Surge Current



# VSKT500-..PbF, VSKH500-..PbF, VSKL500-..PbF

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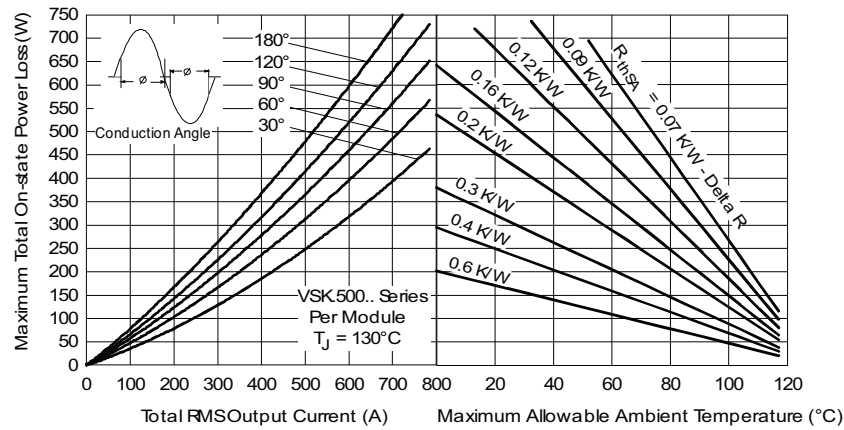


Fig. 7 - On-State Power Loss Characteristics

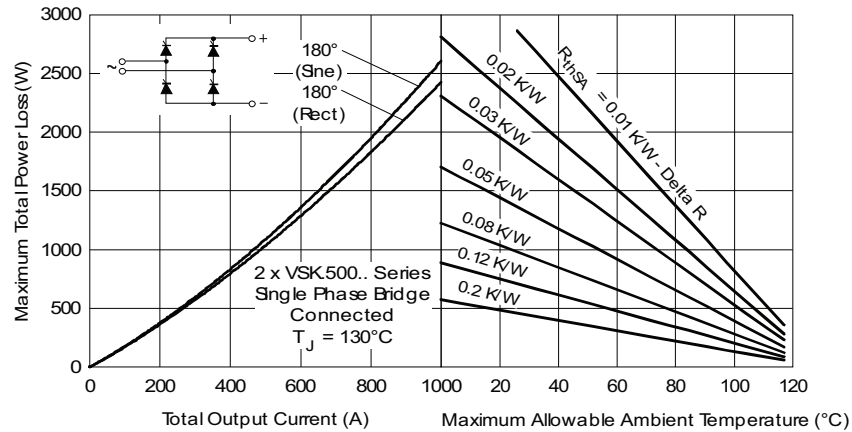


Fig. 8 - On-State Power Loss Characteristics

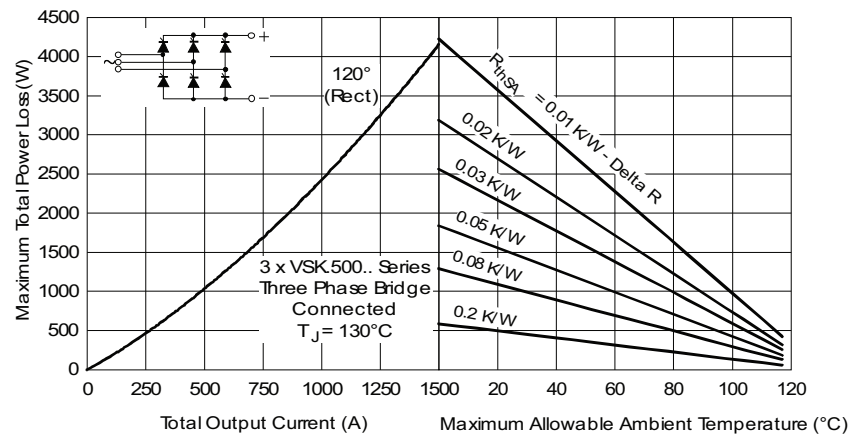


Fig. 9 - On-State Power Loss Characteristics

# VSKT500-..PbF, VSKH500-..PbF, VSKL500-..PbF

Vishay Semiconductors Thyristor/Diode and Thyristor/Thyristor  
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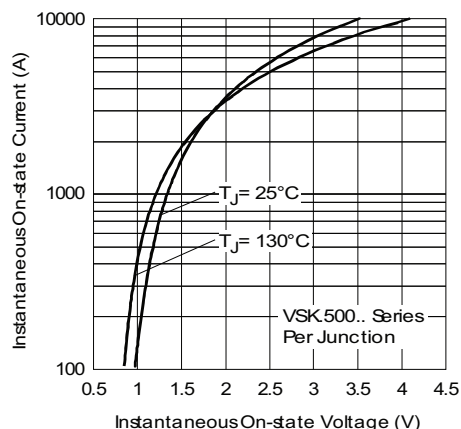


Fig. 10 - On-State Voltage Drop Characteristics

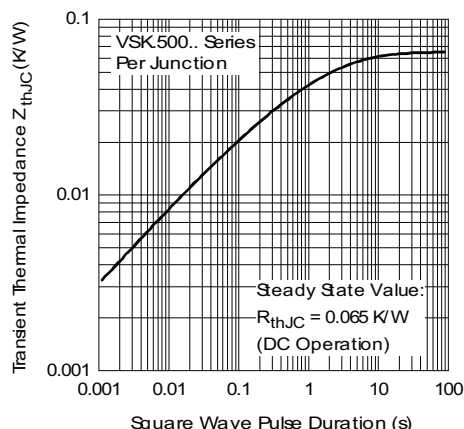


Fig. 11 - Thermal Impedance  $Z_{thJC}$  Characteristics

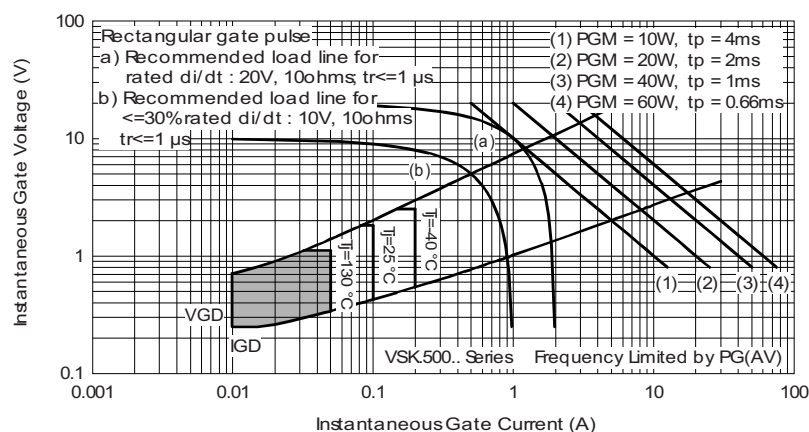


Fig. 12 - Gate Characteristics

## ORDERING INFORMATION TABLE

| Device code | VSK | T                                                          | 500 | - | 16 | PbF |
|-------------|-----|------------------------------------------------------------|-----|---|----|-----|
|             | ①   | ②                                                          | ③   |   | ④  | ⑤   |
| ①           | -   | Module type                                                |     |   |    |     |
| ②           | -   | Circuit configuration (see end of datasheet)               |     |   |    |     |
| ③           | -   | Current rating                                             |     |   |    |     |
| ④           | -   | Voltage code x 100 = $V_{RRM}$ (see Voltage Ratings table) |     |   |    |     |
| ⑤           | -   | Lead (Pb)-free                                             |     |   |    |     |

### Note

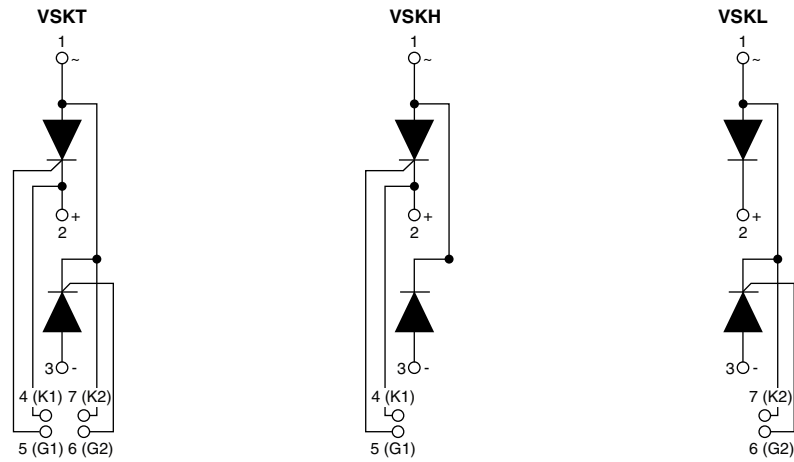
- To order the optional hardware go to [www.vishay.com/doc?95172](http://www.vishay.com/doc?95172)



# VSKT500-..PbF, VSKH500-..PbF, VSKL500-..PbF

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## CIRCUIT CONFIGURATION



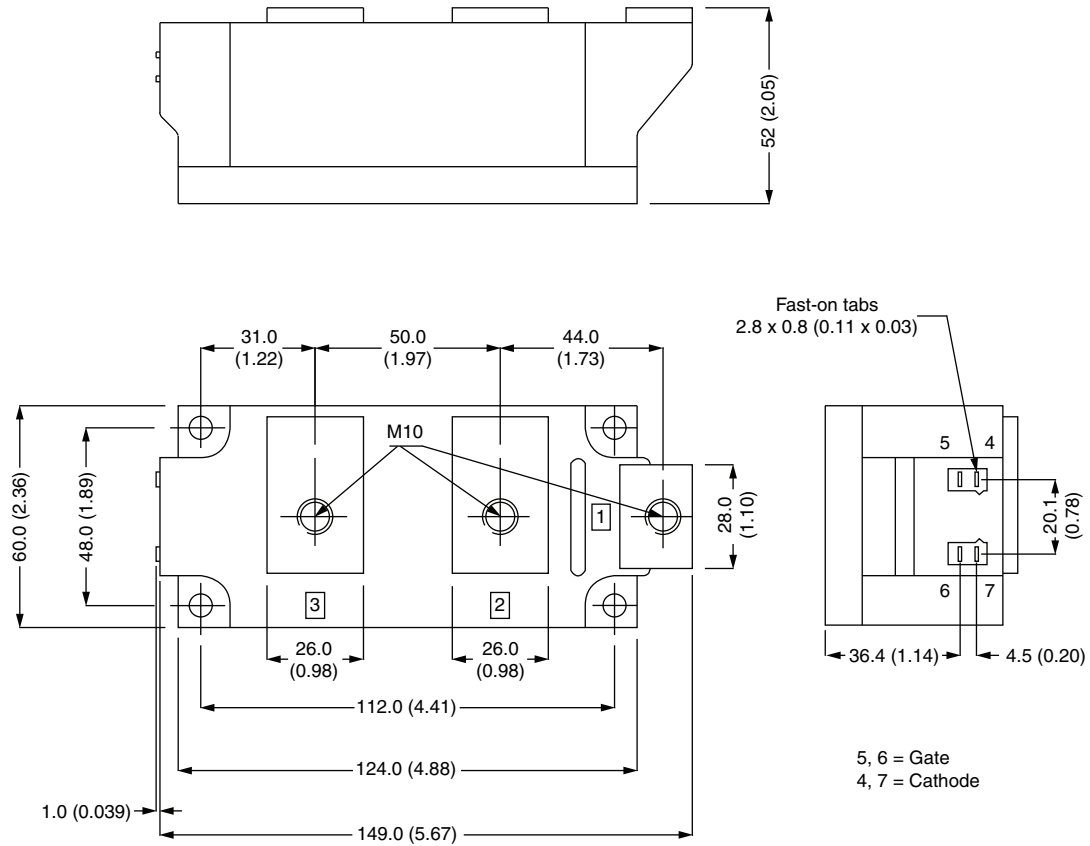
## LINKS TO RELATED DOCUMENTS

Dimensions

[www.vishay.com/doc?95283](http://www.vishay.com/doc?95283)

## Super MAGN-A-PAK Thyristor/Diode

**DIMENSIONS** in millimeters (inches)







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Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

### Офис по работе с юридическими лицами:

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